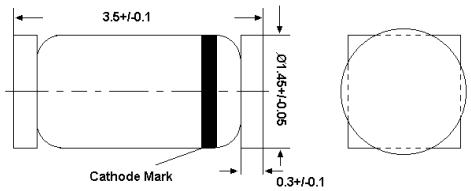
LS4448PF

Silicon Epitaxial Planar Switching Diode

Fast switching diode in QuadroMELF case
especially suited for automatic surface mounting.
Identical electrically to standard JEDEC 1N4448.

LS-34



QuadroMELF
Dimensions in mm

Features

• Lead Free

Absolute Maximum Ratings (T_a = 25℃)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	100	V
Reverse Voltage	V_R	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Surge Forward Current at t < 1 s	I_{FSM}	500	mA
Power Dissipation	P_D	500	mW
Junction Temperature	T_j	175	℃
Storage Temperature Range	T_{stg}	- 65 to + 175	℃

Thermal Characteristics

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient [1)]	$R_{\theta JA}$	300	℃/W

[1)] Valid provided that electrodes are kept at ambient temperature.

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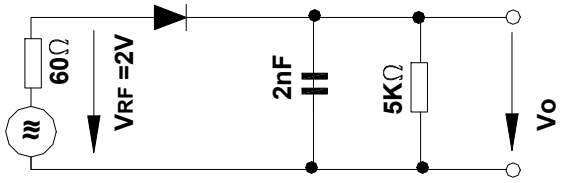
Characteristics at T_a = 25℃

Parameter	Symbol	Min.	Max.	Unit
Forward Voltage at I_F = 5 mA at I_F = 100 mA	V_F	0.62 -	0.72 1	V
Reverse Current at V_R = 20 V at V_R = 75 V	I_R	- -	25 5	nA µA
Reverse Breakdown Voltage at I_R = 100 µA	$V_{(BR)R}$	100	-	V
Capacitance at V_R = 0 V, f = 1 MHz	C_{tot}	-	4	pF
Reverse Recovery Time at I_F = 10 mA to I_R = 1 mA, V_R = 6 V, R_L = 100 Ω	t_{rr}	-	4	ns



Rectification Efficiency Measurement Circuit

Electrical Characteristics Curve

Fig 1. Power Derating Curve

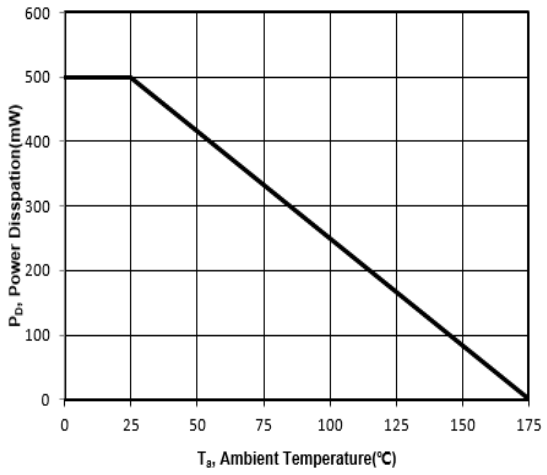


Fig 2. Forward Characteristic Curve

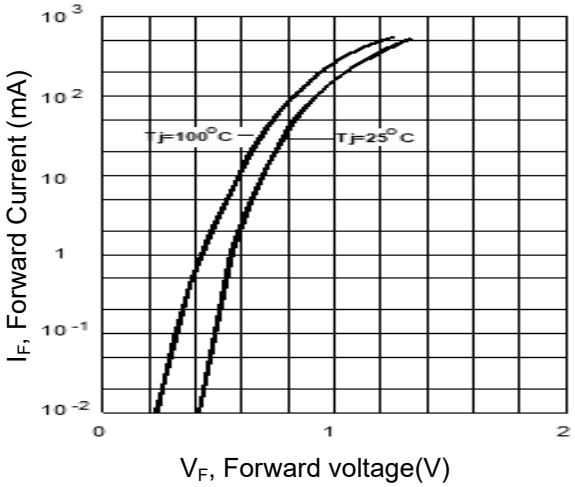


Fig 3. Reverse Characteristic Curve

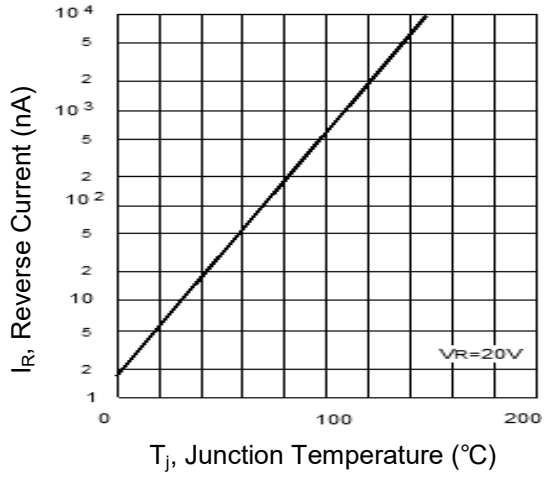


Fig 4. Junction Capacitance

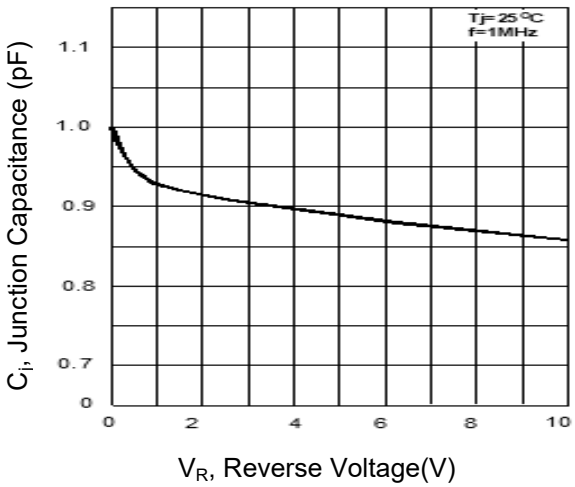
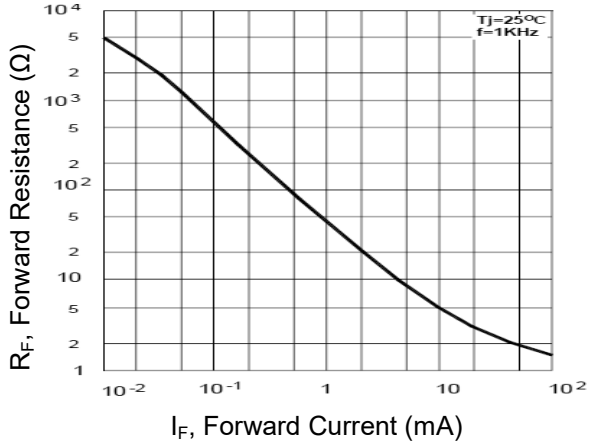


Fig 5. Forward Resistance



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